

High Voltage Power Transistors DPAK For Surface Mount Applications

Designed for line operated audio output amplifier, SWITCHMODE $^{\text{\tiny M}}$ power supply drivers and other switching applications.

- Lead Formed for Surface Mount Applications in Plastic Sleeves (No Suffix)
- Straight Lead Version in Plastic Sleeves ("-1" Suffix)
- Lead Formed Version in 16 mm Tape and Reel ("T4" Suffix)
- Electrically Similar to Popular TIP47, and TIP50
- 250 and 400 V (Min) V_{CEO(sus)}
- 1 A Rated Collector Current

MAXIMUM RATINGS

Rating	Symbol	MJD47	MJD50	Unit		
Collector–Emitter Voltage	V _{CEO}	250 400		Vdc		
Collector-Base Voltage	V _{CB}	350 500		Vdc		
Emitter–Base Voltage	V _{EB}	5		5 Vd		Vdc
Collector Current — Continuous Peak	IC	1 2				Adc
Base Current	I _B	0.6		Adc		
Total Power Dissipation @ T _C = 25°C Derate above 25°C	P _D	15 0.12		Watts W/°C		
Total Power Dissipation* @ T _A = 25°C Derate above 25°C	P _D	1.56 0.0125		Watts W/°C		
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +150		°C		

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	8.33	°C/W
Thermal Resistance, Junction to Ambient*	$R_{\theta JA}$	80	°C/W
Lead Temperature for Soldering Purpose	TL	260	°C

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit		
OFF CHARACTERISTICS						
Collector–Emitter Sustaining Voltage (1) MJD4 (I _C = 30 mAdc, I _B = 0) MJD5	OLO(303)	250 400	_	Vdc		
		_	0.2 0.2	mAdc		

*When surface mounted on minimum pad sizes recommended.

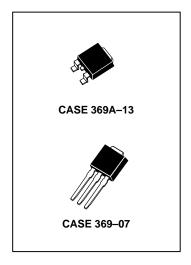
(1) Pulse Test: Pulse Width \leq 300 $\mu \dot{s}$, Duty Cycle \leq 2%.

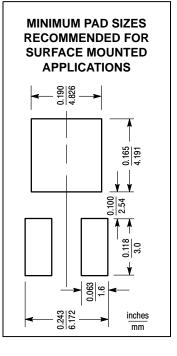
(continued)

MJD47* MJD50*

*ON Semiconductor Preferred Device

NPN SILICON
POWER TRANSISTORS
1 AMPERE
250, 400 VOLTS
15 WATTS





Preferred devices are ON Semiconductor recommended choices for future use and best overall value.

ELECTRICAL CHARACTERISTICS – continued (T_C = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS — continued	,				II.
Collector Cutoff Current $(V_{CE} = 350 \text{ Vdc}, V_{BE} = 0)$ $(V_{CE} = 500 \text{ Vdc}, V_{BE} = 0)$	MJD47 MJD50	I _{CES}	_	0.1 0.1	mAdc
Emitter Cutoff Current (V _{BE} = 5 Vdc, I _C = 0)		I _{EBO}	_	1	mAdc
ON CHARACTERISTICS (1)					
DC Current Gain $(I_C = 0.3 \text{ Adc}, V_{CE} = 10 \text{ Vdc})$ $(I_C = 1 \text{ Adc}, V_{CE} = 10 \text{ Vdc})$		h _{FE}	30 10	150 —	_
Collector–Emitter Saturation Voltage ($I_C = 1$ Adc, $I_B = 0.2$ Adc)		V _{CE(sat)}	_	1	Vdc
Base–Emitter On Voltage (I _C = 1 Adc, V _{CE} = 10 Vdc)		V _{BE(on)}	_	1.5	Vdc
DYNAMIC CHARACTERISTICS					
Current Gain — Bandwidth Product $(I_C = 0.2 \text{ Adc}, V_{CE} = 10 \text{ Vdc}, f = 2 \text{ MHz})$		f _T	10	_	MHz
Small–Signal Current Gain (I _C = 0.2 Adc, V _{CE} = 10 Vdc, f = 1 kHz)		h _{fe}	25	_	_

⁽¹⁾ Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.

TYPICAL CHARACTERISTICS

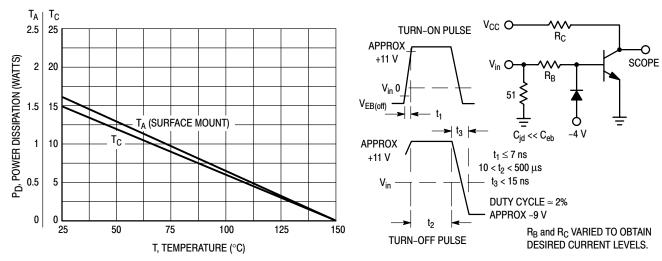


Figure 1. Power Derating Figure 2. Switching Time Equivalent Circuit

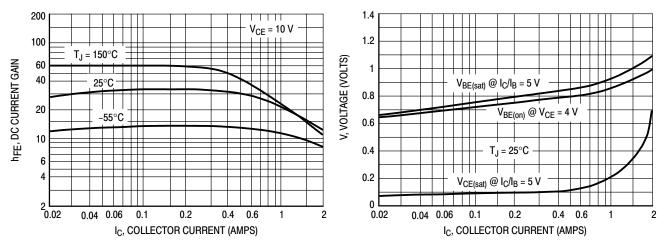


Figure 3. DC Current Gain

Figure 4. "On" Voltages

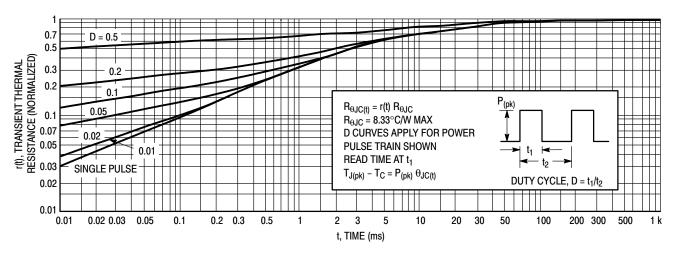


Figure 5. Thermal Response

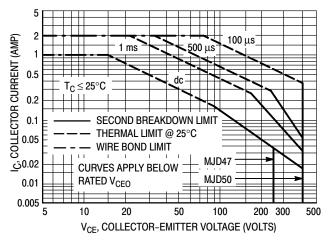


Figure 6. Active Region Safe Operating Area

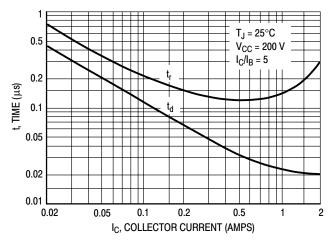


Figure 7. Turn-On Time

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate I_C-V_{CE} limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 6 is based on $T_{J(pk)} = 150^{\circ}C$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \le 150^{\circ}C$. $T_{J(pk)}$ may be calculated from the data in Figure 5. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

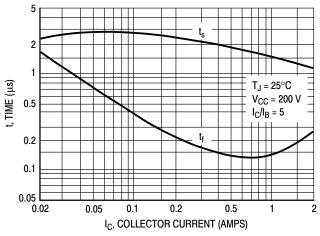
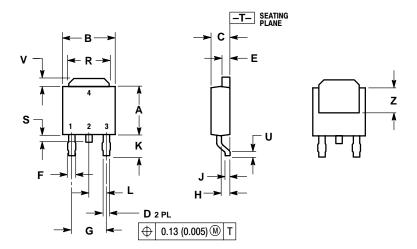


Figure 8. Turn-Off Time

PACKAGE DIMENSIONS

DPAK CASE 369A-13 ISSUE AA

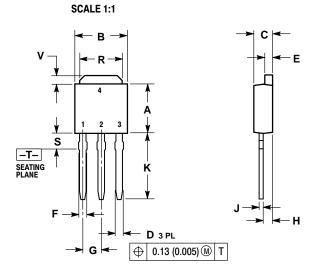


- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIM	ETERS
DIM	MIN	MAX	MIN	MAX
Α	0.235	0.250	5.97	6.35
В	0.250	0.265	6.35	6.73
С	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.033	0.040	0.84	1.01
F	0.037	0.047	0.94	1.19
G	0.180	BSC	4.58 BSC	
Н	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.102	0.114	2.60	2.89
L	0.090 BSC		2.29 BSC	
R	0.175	0.215	4.45	5.46
S	0.020	0.050	0.51	1.27
U	0.020		0.51	
٧	0.030	0.050	0.77	1.27
7	0.138		3.51	

PACKAGE DIMENSIONS

DPAK CASE 369-07 **ISSUE M**



- NOTES:
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	INCHES		MILLIN	IETERS
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G	0.090 BSC		2.29 BSC	
Н	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.175	0.215	4.45	5.46
S	0.050	0.090	1.27	2.28
V	0.030	0.050	0.77	1 27



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